

L Number	Hits	Search Text	DB	Time stamp
1	1018	resistance adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:24
2	60	programmable adj conductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:24
3	64963	low adj resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:25
4	7	(resistance adj memory) and (programmable adj conductor) and (low adj resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:25
5	206	(resistance adj memory) and discharg\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:25
7	63	((resistance adj memory) and discharg\$3) and precharg\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:26
8	2	(programmable adj conductor) and (((resistance adj memory) and discharg\$3) and precharg\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:27
9	324	365/100	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:27
10	42	365/100 and (resistance adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:27
11	1	(365/100 and (resistance adj memory)) and (programmable adj conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:27
12	522	365/\$.ccls. and (resistance adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:28
13	4	(365/\$.ccls. and (resistance adj memory)) and (programmable adj conductor) and (low adj resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:28
14	4726	365/203	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:28
15	24	365/203 and (resistance adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 13:28

16	0	(365/203 and (resistance adj memory)) and (programmable adj conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/05 13:29
17	13	365/185.25 and (resistance adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/05 13:29
18	0	(365/185.25 and (resistance adj memory)) and (programmable adj conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/05 13:29
19	11	365/204 and (resistance adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/05 13:29
20	0	(365/204 and (resistance adj memory)) and (programmable adj conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/05 13:29
21	4105	365/226	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/05 13:29
22	18	365/226 and (resistance adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/05 13:29
23	0	(365/226 and (resistance adj memory)) and (programmable adj conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/05 13:30
24	16	(programmable adj conductor) and (low adj resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/05 13:30